

## 1. General description

Silicon Carbide Schottky diode in a TO220-2L plastic package, designed for high frequency switched-mode power supplies.



## 2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

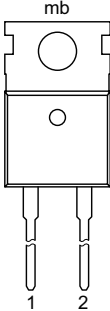

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                       | Conditions  | Values |     |     |     | Unit |
|-------------------------|---------------------------------|---|--------|-----|-----|-----|------|
| Absolute maximum rating |                                 |   |        |     |     |     |      |
| V <sub>RRM</sub>        | repetitive peak reverse voltage |   | 650    |     |     |     | V    |
| I <sub>F(AV)</sub>      | average forward current         | δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 118 °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | 10     |     |     |     | A    |
| T <sub>j</sub>          | junction temperature            |   | 175    |     |     |     | °C   |
| Symbol                  | Parameter                       | Conditions  |        | Min | Typ | Max | Unit |
| Static characteristics  |                                 |   |        |     |     |     |      |
| V <sub>F</sub>          | forward voltage                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 5</a>   |        | -   | 1.5 | 1.7 | V    |
|                         |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 5</a>  |        | -   | 1.8 | 2.2 | V    |
| Dynamic characteristics |                                 |   |        |     |     |     |      |
| Q <sub>r</sub>          | recovered charge                | I <sub>F</sub> = 10 A; dI <sub>F</sub> /dt = 500 A/μs; V <sub>R</sub> = 400 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   |        | -   | 14  | -   | nC   |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                         | Simplified outline  | Graphic symbol  |
|-----|--------|-------------------------------------|---|---|
| 1   | K      | cathode                             |  |  |
| 2   | A      | anode                               |   |   |
| mb  | mb     | mounting base; connected to cathode |   |   |

6. Ordering information

Table 3. Ordering information

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|-------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WNSC2D10650 | TO220-2L     | WNSC2D10650Q          | Tube           | 50                     | SOD59A          | 30-Mar-2015        |

7. Marking

Table 4. Marking codes

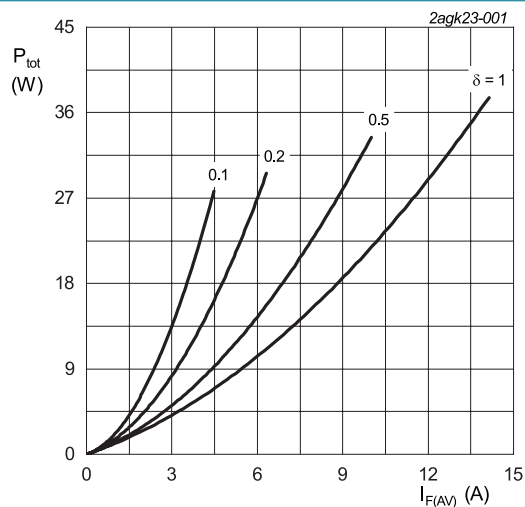
| Type number | Marking codes   |
|-------------|-----------------|
| WNSC2D10650 | WNSC2D<br>10650 |

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

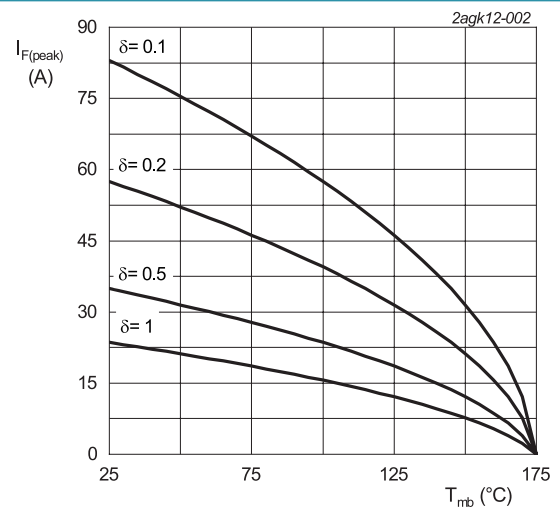
| Symbol      | Parameter                           | Conditions   | Values     | Unit                 |
|-------------|-------------------------------------|--|------------|----------------------|
| $V_{RRM}$   | repetitive peak reverse voltage     |  | 650        | V                    |
| $V_{RWM}$   | crest working reverse voltage       |  | 650        | V                    |
| $V_R$       | reverse voltage                     | DC   | 650        | V                    |
| $I_{F(AV)}$ | average forward current             | $\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 118^\circ\text{C}$ ; Fig. 1; Fig. 2; Fig. 3   | 10         | A                    |
| $I_{FRM}$   | repetitive peak forward current     | $\delta = 0.5$ ; $t_p = 25\ \mu\text{s}$ ; $T_{mb} \leq 118^\circ\text{C}$ ; square-wave pulse | 20         | A                    |
| $I_{FSM}$   | non-repetitive peak forward current | $t_p = 10\ \text{ms}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$ ; sine-wave pulse              | 50         | A                    |
|             |                                     | $t_p = 10\ \mu\text{s}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$ ; square-wave pulse          | 450        | A                    |
| $I^2t$      | $I^2t$ for fusing                   | sine-wave pulse; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 10\ \text{ms}$               | 12.5       | $\text{A}^2\text{s}$ |
| $T_{stg}$   | storage temperature                 |  | -55 to 175 | $^\circ\text{C}$     |
| $T_j$       | junction temperature                |  | 175        | $^\circ\text{C}$     |



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.024\ \text{V}; R_s = 0.1156\ \Omega$$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values**



**Fig. 2. Current derating as a function of mounting base temperature**

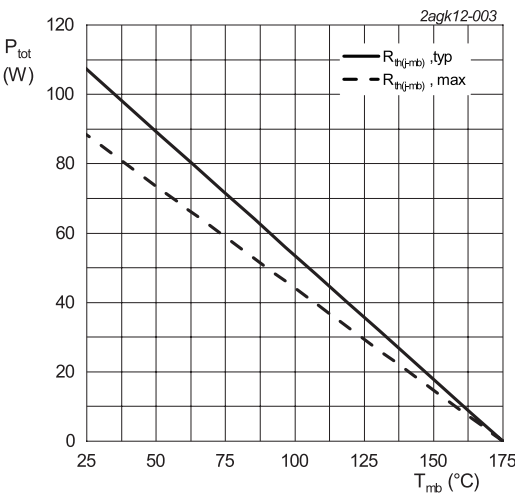


Fig. 3. Total power dissipation as a function of mounting base temperature

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter  | Conditions             |  | Min | Typ | Max | Unit |
|----------------|--|------------------------|--|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base    | <a href="#">Fig. 4</a> |  | -   | -   | 1.7 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient free air | in free air            |  | -   | 60  | -   | K/W  |

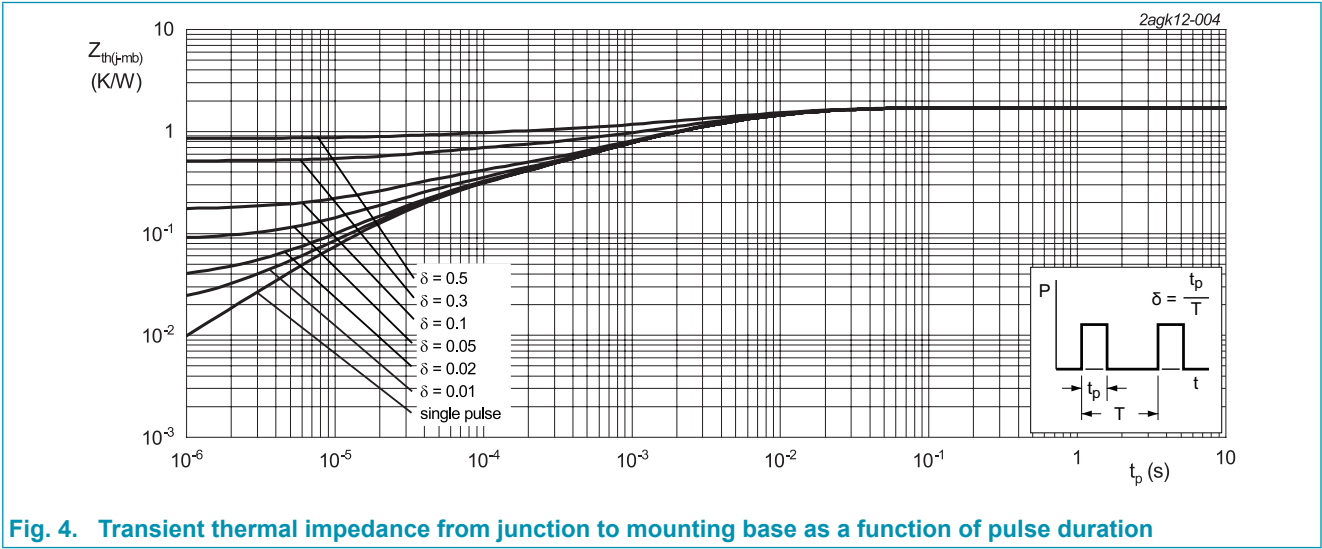
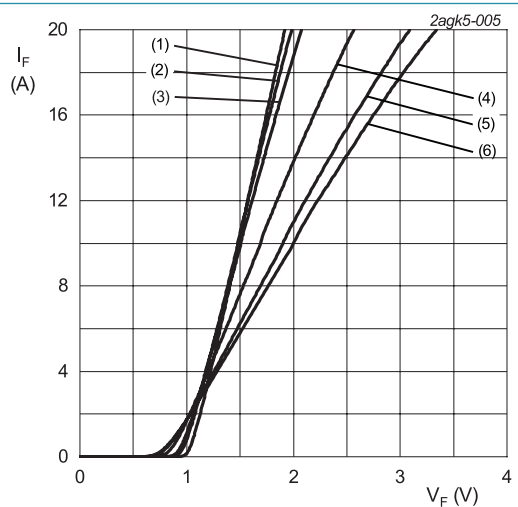


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                       | Conditions  |  | Min | Typ | Max | Unit |
|-------------------------|---------------------------------|---|--|-----|-----|-----|------|
| Static characteristics  |                                 |   |  |     |     |     |      |
| V <sub>F</sub>          | forward current                 | I <sub>F</sub> = 10 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 5</a>   |  | -   | 1.5 | 1.7 | V    |
|                         |                                 | I <sub>F</sub> = 10 A; T <sub>J</sub> = 150 °C; <a href="#">Fig. 5</a>  |  | -   | 1.8 | 2.2 | V    |
|                         |                                 | I <sub>F</sub> = 10 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 5</a>  |  | -   | 2   | 2.3 | V    |
| I <sub>R</sub>          | reverse current                 | V <sub>R</sub> = 650 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 6</a>  |  | -   | 0.5 | 50  | μA   |
|                         |                                 | V <sub>R</sub> = 650 V; T <sub>J</sub> = 175 °C; <a href="#">Fig. 6</a>   |  | -   | 25  | 250 | μA   |
| Dynamic characteristics |                                 |   |  |     |     |     |      |
| Q <sub>r</sub>          | recovered charge                | I <sub>F</sub> = 10 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>J</sub> = 25 °C; <a href="#">Fig. 7</a> |  | -   | 14  | -   | nC   |
| C <sub>d</sub>          | diode capacitance               | f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>J</sub> = 25 °C   |  | -   | 310 | -   | pF   |
|                         |                                 | f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>J</sub> = 25 °C   |  | -   | 36  | -   | pF   |
|                         |                                 | f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>J</sub> = 25 °C   |  | -   | 32  | -   | pF   |
| E <sub>as</sub>         | non-repetitive avalanche energy | I <sub>R</sub> = 5.5 A; L = 5 mH; T <sub>j(init)</sub> = 25 °C  |  | 75  | -   | -   | mJ   |



V<sub>0</sub> = 1.024 V; R<sub>s</sub> = 0.1156 Ω  
(1) T<sub>J</sub> = -55 °C; typical values  
(2) T<sub>J</sub> = 0 °C; typical values  
(3) T<sub>J</sub> = 25 °C; typical values  
(4) T<sub>J</sub> = 100 °C; typical values  
(5) T<sub>J</sub> = 150 °C; typical values  
(6) T<sub>J</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

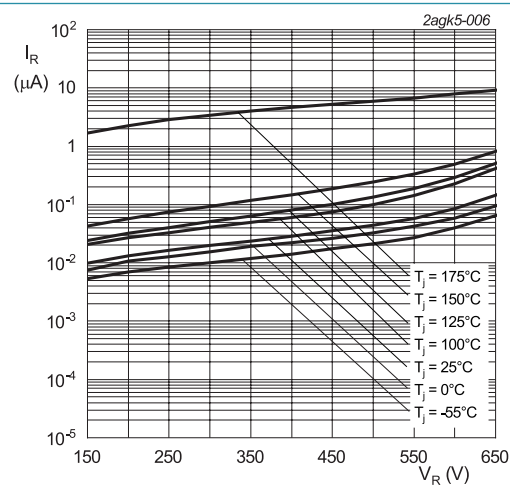


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

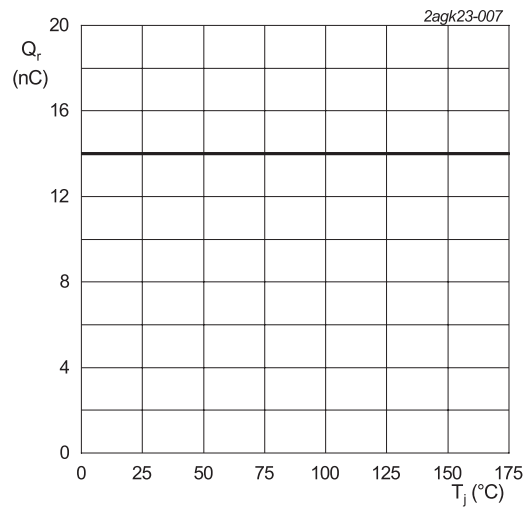
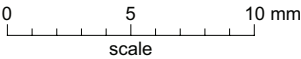
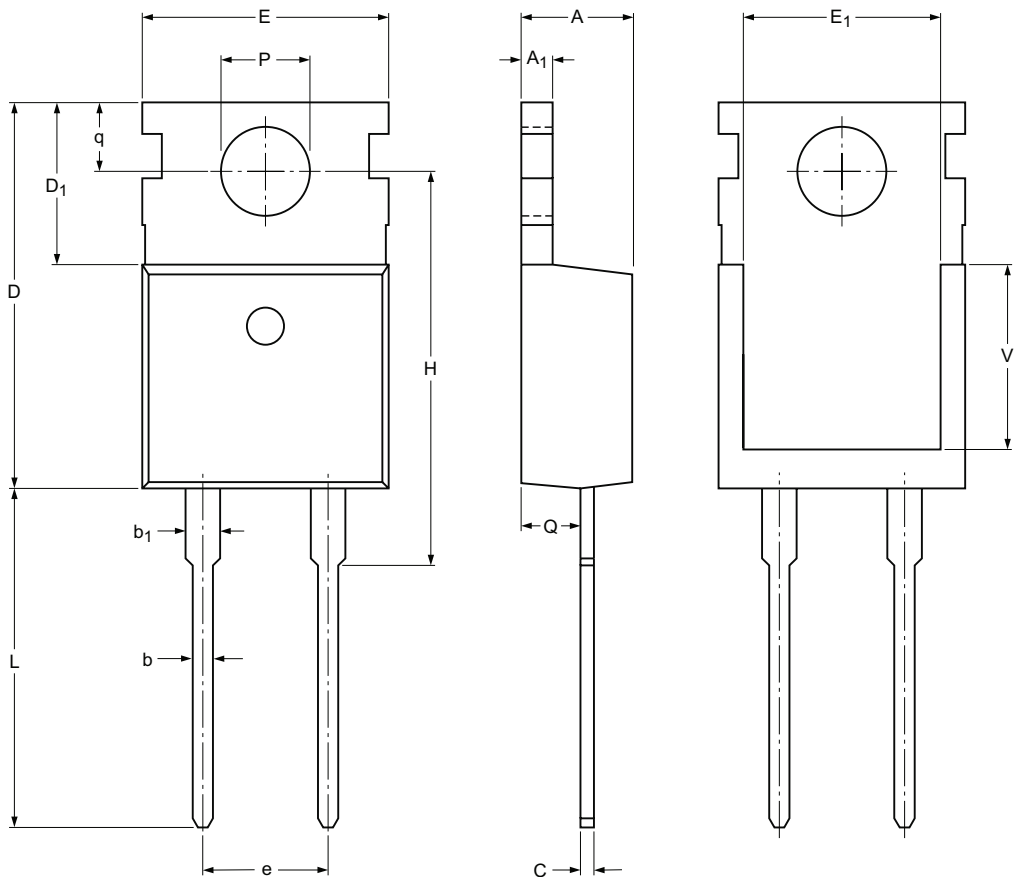


Fig. 7. Recovered charge as a function of junction temperature

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC SOD59A



Dimensions: (mm are the original dimensions)

| Unit | A   | A <sub>1</sub> | b    | b <sub>1</sub> <sup>(1)</sup> | c    | D    | D <sub>1</sub> | E     | e     | H     | L    | P    | Q   | q    | E <sub>1</sub> | V     |
|------|-----|----------------|------|-------------------------------|------|------|----------------|-------|-------|-------|------|------|-----|------|----------------|-------|
| max  | 4.7 | 1.40           | 0.95 | 1.70                          | 0.65 | 15.8 | 6.8            | 10.30 | 5.08  | 16.25 | 15.0 | 3.80 | 2.6 | 2.95 | 8.1            | 6.9   |
| nom  |     |                |      |                               |      |      |                |       | (REF) |       |      |      |     |      |                | (REF) |
| min  | 4.3 | 1.15           | 0.70 | 1.17                          | 0.45 | 15.6 | 6.4            | 9.65  |       | 15.70 | 12.5 | 3.53 | 2.2 | 2.65 | 7.9            |       |

Note  
1. Protruded dambar are included in the dimension.

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| Outline version | References |                   |       |  | European projection | Issue date             |
|-----------------|------------|-------------------|-------|--|---------------------|------------------------|
|                 | IEC        | JEDEC             | JEITA |  |                     |                        |
| SOD59A          |            | TO-220AC (2-lead) |       |  |                     | -15-03-24-<br>15-03-30 |



## 12. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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